



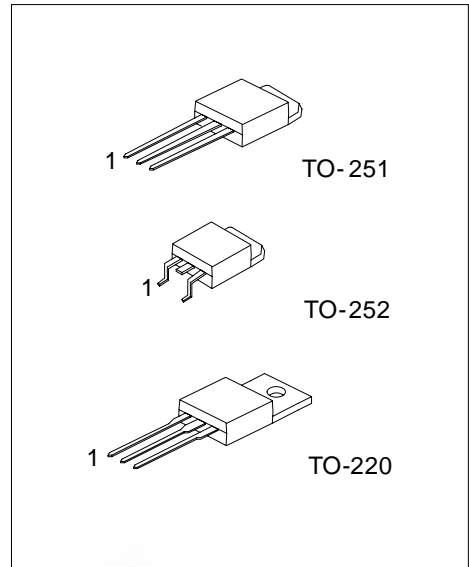
MJE3055T

NPN SILICON TRANSISTOR

HIGH VOLTAGE TRANSISTOR

■ DESCRIPTION

The UTC **MJE3055T** is designed for general purpose of amplifier and switching applications.



*Pb-free plating product number: MJE3055TL

■ ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
MJE3055T-TA3-T	MJE3055TL-TA3-T	TO-220	B	C	E	Tube
MJE3055T-TM3-T	MJE3055TL-TM3-T	TO-251	B	C	E	Tube
MJE3055T-TN3-R	MJE3055TL-TN3-R	TO-252	B	C	E	Tape Reel
MJE3055T-TN3-T	MJE3055TL-TN3-T	TO-252	B	C	E	Tube

<p>MJE3055TL-TA3-T</p> <p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Lead Plating</p>	<p>(1) R: Tape Reel, T: Tube</p> <p>(2) TA3: TO-220, TM3: TO-251, TN3: TO-252</p> <p>(3) L: Lead Free Plating, Blank: Pb/Sn</p>
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■ ABSOLUTE MAXIMUM RATINGS (T_c=25)

(Operating temperature range applies unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V _{CBO}	70	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	5	V
Total Power Dissipation	TO-220	75	W
	TO-251/TO-252	20	W
Collector Current	I _C	10	A
Base Current	I _B	6	A
Junction Temperature	T _J	150	
Storage Temperature	T _{STG}	-55 ~ +150	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_a=25 , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =200mA	60			V
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =10mA	70			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =10mA	5			V
Collector Cut-off Current	I _{CBO}	V _{CB} =70V			1	mA
	I _{CEO}	V _{CE} =30V			700	μA
	I _{CEX}	V _{CE} =70V, V _{EB(OFF)} =1.5V			1	mA
Emitter Cut-off Current	I _{EBO}	V _{EB} =5V			5	mA
Collector-Emitter Saturation Voltage	V _{CE(SAT)1}	I _C =4A, I _B =0.4A			1.1	V
	V _{CE(SAT)2}	I _C =10A, I _B =3.3A			8	V
Base-Emitter on Voltage	V _{BE(ON)}	V _{CE} =4V, I _C =4A			1.8	V
DC Current Gain	h _{FE1}	I _C =4A, V _{CE} =4V	20			
	h _{FE2}	I _C =4A, V _{CE} =10V	5		100	
Current Gain Bandwidth Product	f _T	V _{CE} =10V, I _C =0.5A, f=1MHz	2			MHZ

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